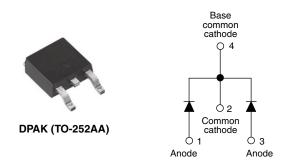
Vishay Semiconductors

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Ultrafast Rectifier, 2 x 3 A FRED Pt[®]



PRIMARY CHARACTERISTICS								
I _{F(AV)}	2 x 3 A							
V _R	200 V							
V _F at I _F	0.9 V							
t _{rr} typ.	See Recovery table							
T _J max.	175 °C							
Package	DPAK (TO-252AA)							
Circuit configuration	Common cathode							

FEATURES

- · Ultrafast recovery time
- · Low forward voltage drop
- · Low leakage current
- 175 °C operating junction temperature



- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

VS-MURD620CT-M3 is the state of the art ultrafast recovery rectifier specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS					
Peak repetitive reverse voltage	V _{RRM}		200	V					
Average rectified forward current per device	I _{F(AV)}	Total device, rated V_R , T_C = 146 °C	6						
Non-repetitive peak surge current	I _{FSM}		50	А					
Peak repetitive forward current per diode	I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 146 °C	6						
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C					

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-				
Forward voltage		I _F = 3 A	- 0.9		1.0				
	VF	I _F = 3 A, T _J = 125 °C	-	0.78	0.96	V			
		I _F = 6 A	-	1	1.2				
		I _F = 6 A, T _J = 125 °C	-	0.89	1.13				
	I _R	$V_{R} = V_{R}$ rated	-	-	5				
Reverse leakage current		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	μA			
Junction capacitance	CT	V _R = 200 V	-	12	-	pF			
Series inductance	Ls	Measured lead to lead 5 mm from package body	-	8.0	-	nH			

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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time		I _F = 1.0 A, dI _F /dt = 50 A/μs, V _R = 30 V		-	-	35			
	t _{rr}	$I_F = 0.5 \text{ A}, I_R = 1.0 \text{ A}, I_F$	-	-	25				
		T _J = 25 °C		-	19	-	ns		
		T _J = 125 °C	l _F = 3 A dl _F /dt = 200 A/µs	-	26	-			
Pools receivers ourrent	1	T _J = 25 °C		-	3.1	-	_		
Peak recovery current	I _{RRM}	T _J = 125 °C	$V_{\rm B} = 160 \text{ V}$	-	4.6	-	A		
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	30	-			
		T _J = 125 °C]	-	60	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C				
Thermal resistance, junction to case per leg	R _{thJC}		-	-	9.0					
Thermal resistance, junction to ambient per leg	R _{thJA}		-	-	80	°C/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	-	-					
Waight			-	0.3	-	g				
Weight			-	0.01	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style DPAK (TO-252AA)	MURD620CT							



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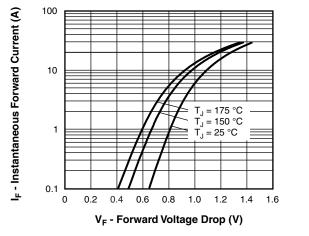


Fig. 1 - Typical Forward Voltage Drop Characteristics

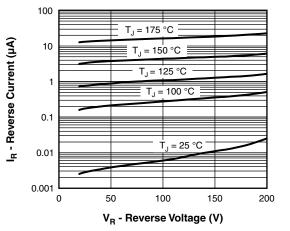


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

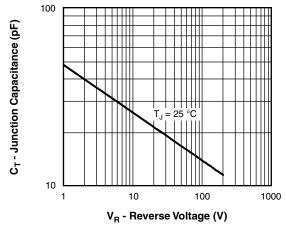
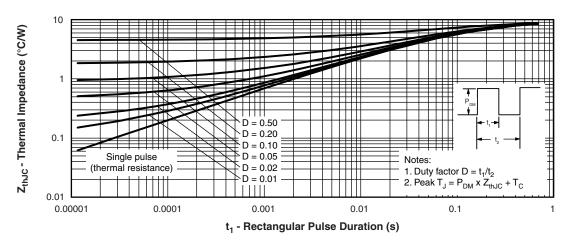


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





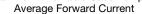
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180 Allowable Case Temperature (°C) 170 160 DC 150 Square wave (D = 0.50) Rated V_R applied 140 130 See note (1) 120 3 4 0 1 2 5 I_{F(AV)} - Average Forward Current (A)

Fig. 5 - Maximum Allowable Case Temperature vs.



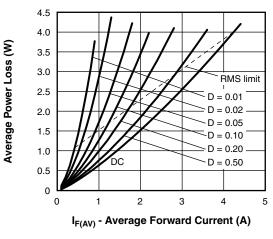


Fig. 6 - Forward Power Loss Characteristics

Note

- ⁽¹⁾ Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$;
- $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{I} \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

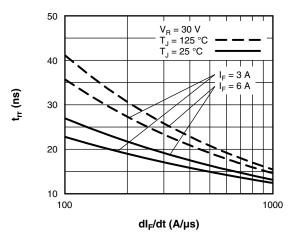


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

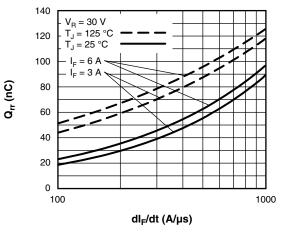


Fig. 8 - Typical Stored Charge vs. dl_F/dt

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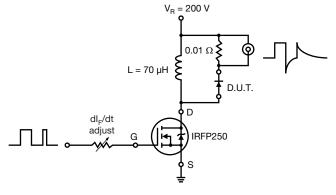


Fig. 9 - Reverse Recovery Parameter Test Circuit

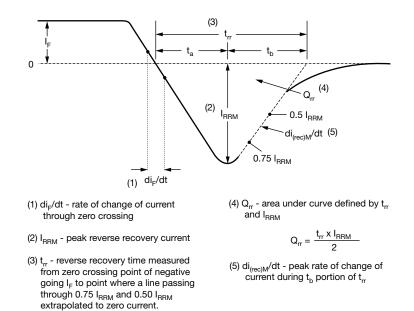
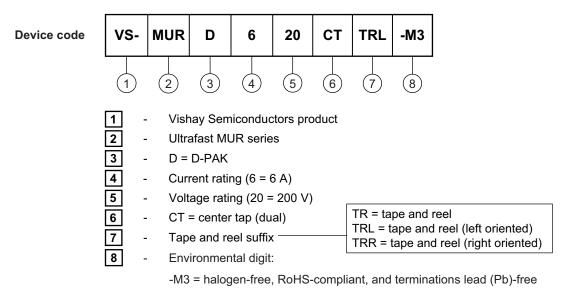


Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

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ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-MURD620CT-M3	75	3000	Antistatic plastic tube						
VS-MURD620CTTR-M3	2000	2000	13" diameter reel						
VS-MURD620CTTRL-M3	3000	3000	13" diameter reel						
VS-MURD620CTTRR-M3	3000	3000	13" diameter reel						

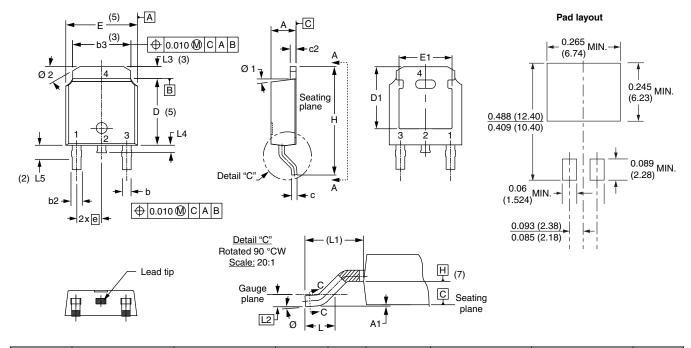
LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95627						
Part marking information	www.vishay.com/doc?95176						
Packaging information	www.vishay.com/doc?95033						





D-PAK (TO-252AA) "M"

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	INCHES			NOTES SYMBOL		MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	2.18	2.39	0.086	0.094			е	2.29	BSC	0.090	BSC		
A1	-	0.13	-	0.005			Н	9.40	10.41	0.370	0.410		
b	0.64	0.89	0.025	0.035			L	1.40	1.78	0.055	0.070		
b2	0.76	1.14	0.030	0.045			L1	2.74	BSC	0.108	REF.		
b3	4.95	5.46	0.195	0.215	3		L2	0.51	BSC	0.020	BSC		
с	0.46	0.61	0.018	0.024			L3	0.89	1.27	0.035	0.050	3	
c2	0.46	0.89	0.018	0.035			L4	-	1.02	-	0.040		
D	5.97	6.22	0.235	0.245	5		L5	1.14	1.52	0.045	0.060	2	
D1	5.21	-	0.205	-	3		Ø	0°	10°	0°	10°		
E	6.35	6.73	0.250	0.265	5		Ø1	0°	15°	0°	15°		
E1	4.32	-	0.170	-	3		Ø2	25°	35°	25°	35°		

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension uncontrolled in L5

⁽³⁾ Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad

(4) Section C - C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip

(5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁶⁾ Dimension b1 and c1 applied to base metal only

⁽⁷⁾ Datum A and B to be determined at datum plane H

⁽⁸⁾ Outline conforms to JEDEC[®] outline TO-252AA



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